

TOSHIBA INFRARED LED GaAlAs INFRARED EMITTER

# TLN203

INFRARED LED FOR PHOTODIODES

Unit : mm

OPTO-ELECTRONIC SWITCHES

TAPE AND CARD READERS

ROTARY ENCODERS

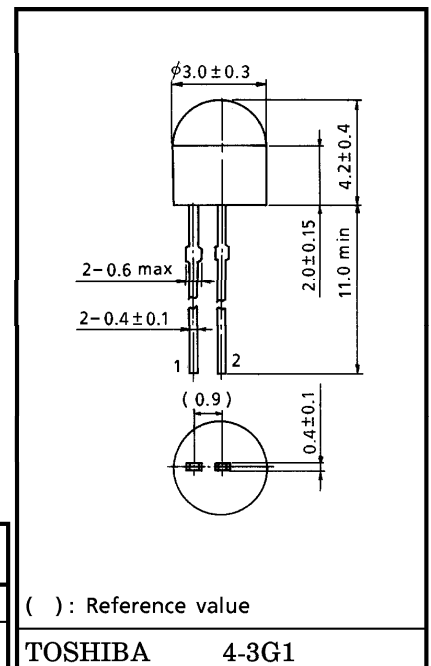
FDD (FLOPPY DISK DRIVE) DETECTION

- High radiant intensity
- Ideal for use in combination with TPS613 phototransistor

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward Current	$I_F$	50	mA
Forward Current Derating (Ta > 25°C)	$\Delta I_F$	-0.67	mA / °C
Pulse Forward Current (Note)	$I_{FP}$	1	A
Reverse Voltage	$V_R$	5	V
Operating Temperature	$T_{opr}$	-20~75	°C
Storage Temperature	$T_{stg}$	-30~100	°C

(Note) : Pulse Width  $\leq 100 \mu s$ , repetitive frequency = 100 Hz

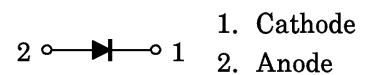


( ) : Reference value

TOSHIBA 4-3G1

Weight : 0.09 g (typ.)

PIN CONNECTION



OPTICAL AND ELECTRICAL CHARACTERISTICS (Ta = 25°C)

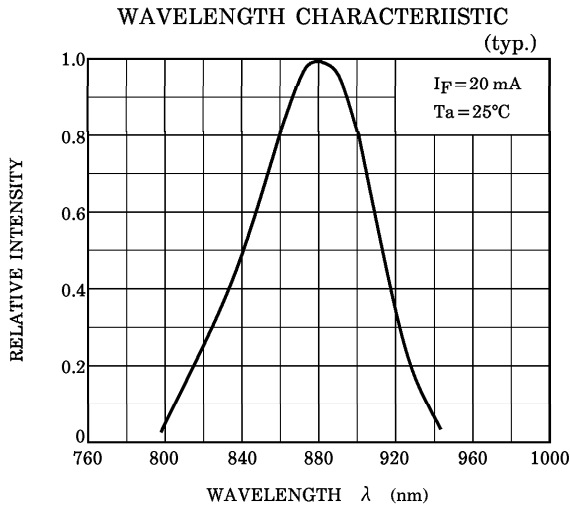
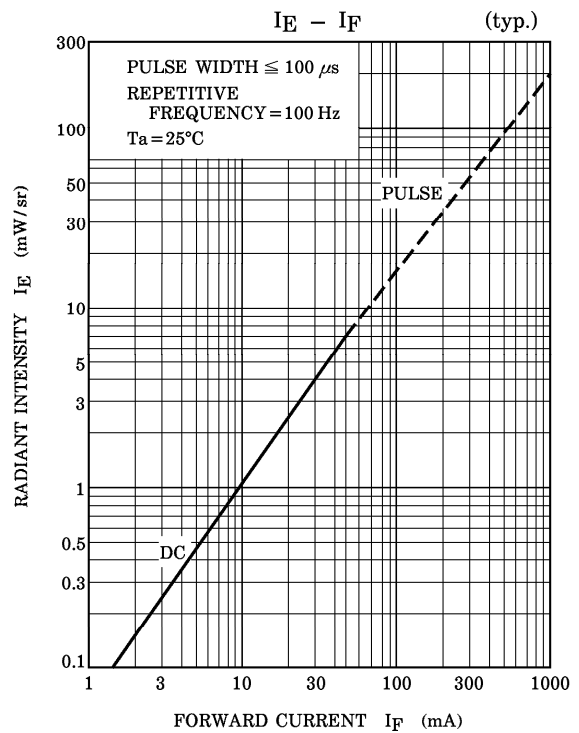
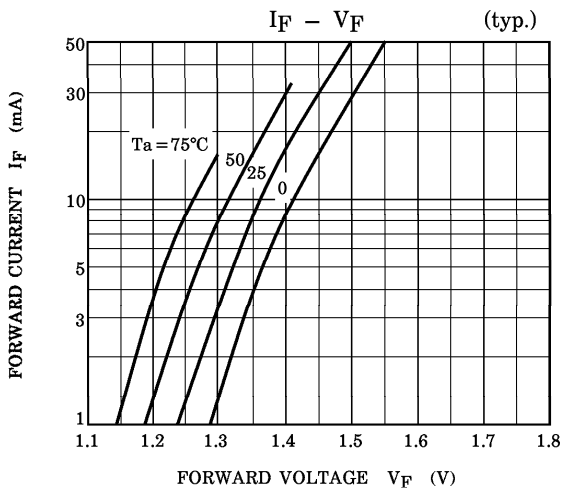
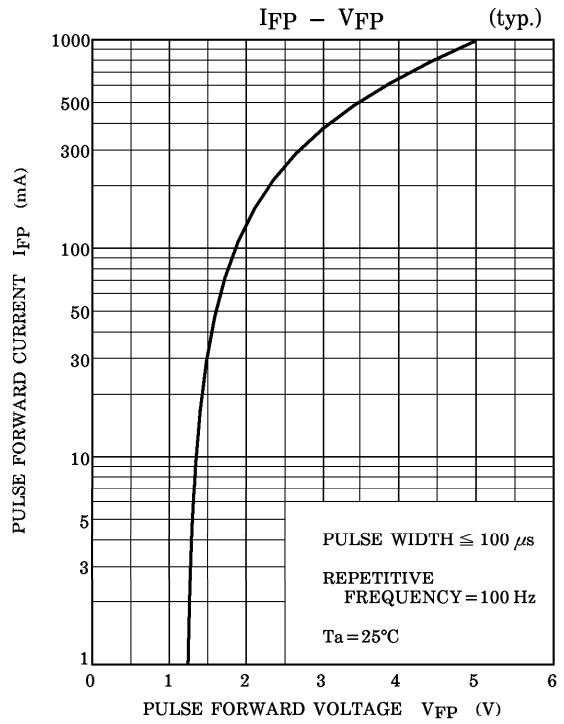
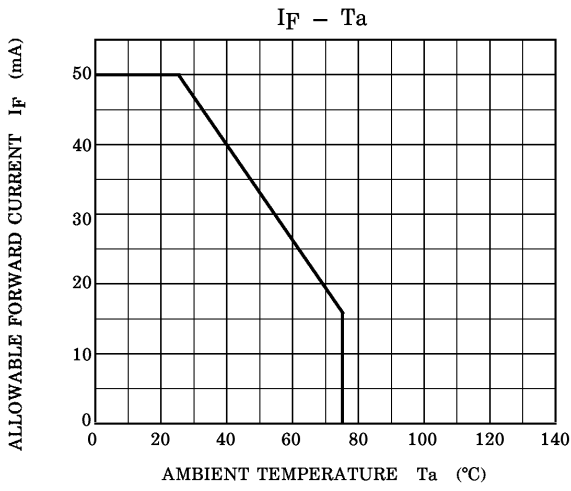
CHARACTERISTIC	SYMBOL	TEST CONDITION	Min	Typ.	Max	UNIT
Forward Voltage	$V_F$	$I_F = 50 \text{ mA}$	—	1.45	1.9	V
Reverse Current	$I_R$	$V_R = 5 \text{ V}$	—	—	10	$\mu A$
Radiant Intensity	$I_E$	$I_F = 20 \text{ mA}$	1.0	—	—	mW / sr
Radiant Power	$P_O$	$I_F = 20 \text{ mA}$	—	3.5	—	mW
Capacitance	$C_T$	$V_R = 0, f = 1 \text{ MHz}$	—	60	—	pF
Peak Emission Wavelength	$\lambda_P$	$I_F = 20 \text{ mA}$	—	880	—	nm
Spectral Line Half Width	$\Delta \lambda_P$	$I_F = 20 \text{ mA}$	—	80	—	nm
Half Value Angle	$\theta_{\frac{1}{2}}$	$I_F = 20 \text{ mA}$	—	$\pm 35$	—	°

**PRECAUTIONS**

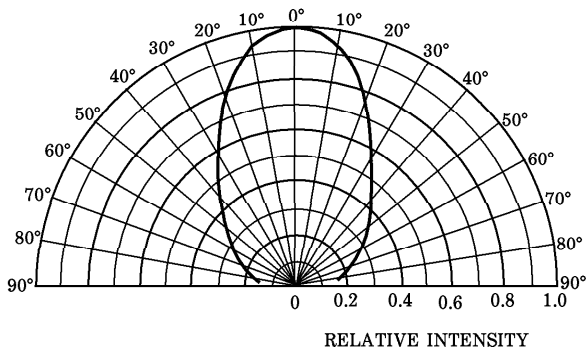
Please be careful of the followings.

1. Soldering must be performed under the lead stopper.
2. Soldering temperature : 260°C max  
Soldering time : 3 s max
3. When forming the leads, bend each lead under the 2 mm from the body of the device.  
Soldering must be performed after the leads have been formed.
4. Radiation intensity falls over time due to the current which flows in the infrared LED.  
When designing a circuit, take into account this change in radiant power over time.  
The ratio of fluctuation in radiation intensity to fluctuation in optical output is 1 : 1.

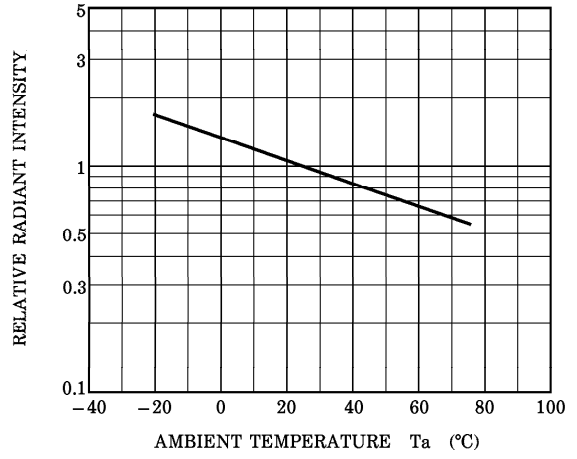
$$\frac{I_E(t)}{I_E(0)} = \frac{P_O(t)}{P_O(0)}$$



RADIATION PATTERN (typ.)  
( $T_a = 25^\circ\text{C}$ )



RELATIVE  $I_E - T_a$  (typ.)



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